RENESAS

RJK2017DPE

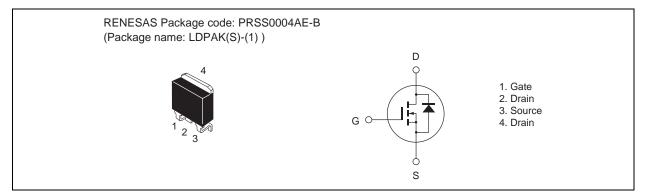
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1589-0400 Rev.4.00 Dec 02, 2009

Features

- Low on-resistance •
 - $R_{DS(on)}$ = 0.036 Ω typ. (at I_D = 22.5 A, V_{GS} = 10 V, Ta = 25 °C)
- Low leakage current
- High speed switching •

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit	
Drain to source voltage	V _{DSS}	200	V	
Gate to source voltage	V _{GSS}	±30	V	
Drain current	ID	45	А	
Drain peak current	Note1 D (pulse)	135	А	
Body-drain diode reverse drain current	I _{DR}	45	А	
Body-drain diode reverse drain peak current	Note1 I _{DR (pulse)}	135	А	
Avalanche current	I _{AP} ^{Note3}	12	А	
Avalanche energy	E _{AR} Note3	9.6	mJ	
Channel dissipation	Pch Note2	100	W	
Channel to case thermal impedance	θch-c	1.25	°C/W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	۵°	

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

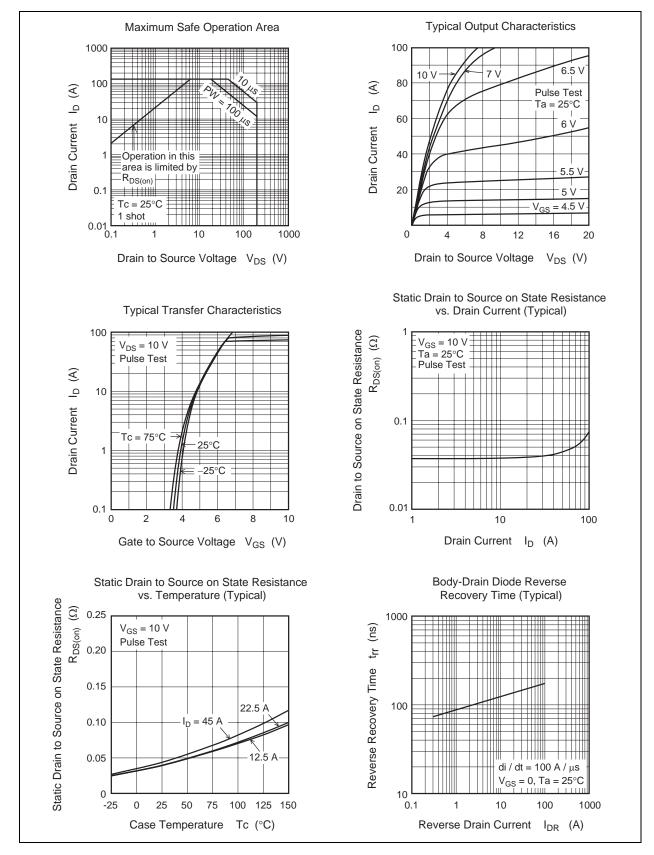
3. STch = 25° C, Tch $\leq 150^{\circ}$ C

Electrical Characteristics

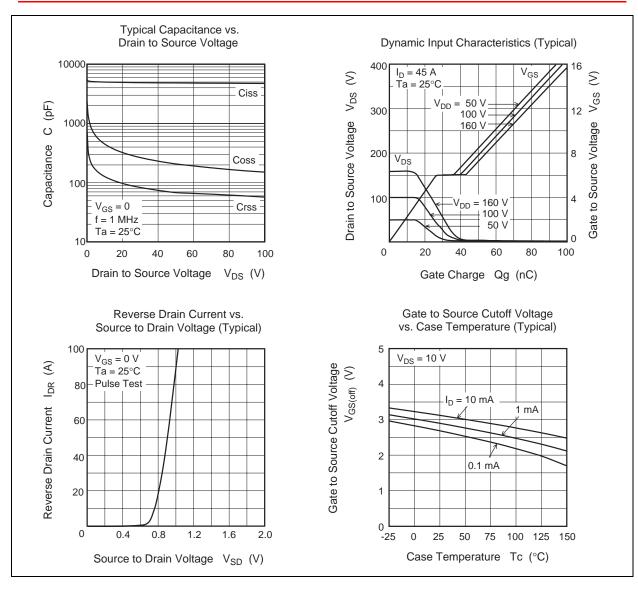
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Мах	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	200		—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_		1	μΑ	$V_{DS} = 200 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	—	±1	μΑ	$V_{GS} = \pm 30$ V, $V_{DS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	2	_	4	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R _{DS(on)}	_	0.036	0.047	Ω	$I_D = 22.5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	4800	_	pF	$V_{DS} = 25 V$ $V_{GS} = 0$ f = 1 MHz
Output capacitance	Coss	—	290	—	pF	
Reverse transfer capacitance	Crss	—	90	—	pF	
Turn-on delay time	t _{d(on)}	—	50	—	ns	$I_{D} = 22.5 \text{ A} \\ V_{GS} = 10 \text{ V} \\ R_{L} = 4.5 \Omega \\ \text{Rg} = 10 \Omega$
Rise time	tr	—	40	—	ns	
Turn-off delay time	t _{d(off)}		95	—	ns	
Fall time	t _f		40	—	ns	
Total gate charge	Qg		66	—	nC	V _{DD} = 160 V
Gate to source charge	Qgs	—	26	—	nC	V _{GS} = 10 V I _D = 45 A
Gate to drain charge	Qgd	—	16	—	nC	
Body-drain diode forward voltage	V_{DF}	_	0.88	1.35	V	$I_{F} = 45 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t _{rr}		150		ns	$I_F = 45 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

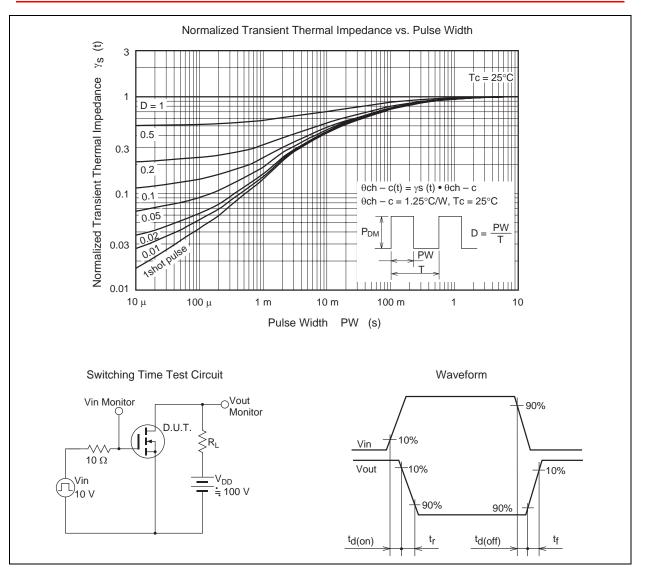
Notes: 4. Pulse test

Main Characteristics

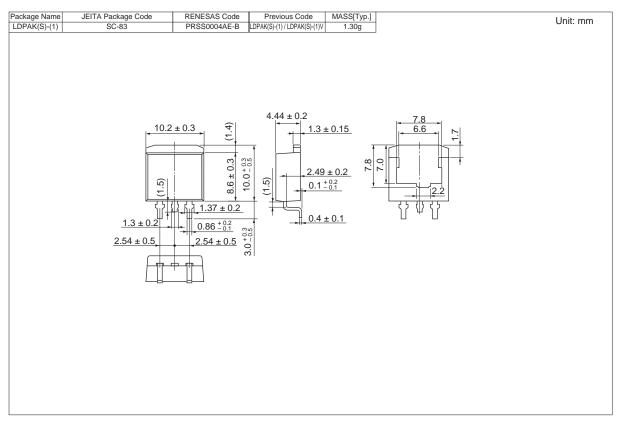


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Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK2017DPE-00-J3	1000 pcs	Taping

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http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

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